Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	@pn="5801075"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 10:17
S1	571	@ad<"20040205" and (silicon adj germanium) and (strained adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:22
S2	523	S1 and (first insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:37
S3	520	S2 and (second insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:37
S4	27	S1 and (first adj insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:37
S5	19	S4 and (second adj insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:37
S6	1	@pn="6306722"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:24
S7	1	@pn="4998150"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:26

S8	1	@pn="5102816"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:26
S9	30	("3472712" | "3475234" | "3615934" | "4072545" | "4204894" | "4356040" | "4384301" | "4488351" | "4530150" | "4642878" | "4722909" | "4728617" | "4735916" | "4740484" | "4744859" | "4745086" | "4753898" | "4760033" | "4764477" | "4808544" | "4818714" | "4818715" | "4826782" | "4837180" | "4843023" | "4855247" | "4873557" | "4998150").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 14:26
S10	28	("5108954" | "5120666" | "5168072" | "5200352" | "5202754" | "5258637" | "5264382" | "5320974" | "5321286" | "5346834" | "5374575" | "5391510" | "5393685" | "5420048" | "5429956" | "5451798" | "5481133" | "5482877" | "5491099" | "5497019" | "5516707" | "5581101" | "5593907" | "5595919" | "5607884" | "5612546" | "5612552" | "5654570").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:28
S11	27	("56751598" | "5675185" | "5689136" | "5716861" | "5733792" | "5736446" | "5753542" | "5789792" | "5793090" | "5811323" | "5825066" | "5851869" | "5856225" | 5858843| "5908307" | "5915182" | "5915196" | "5936280" | "5953616" | "5960270" | "5985726" | "6008111" | "6017808" | "6025254" | "6031269" | "6030863" | "6033958" | "6037204").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 15:23
S12	28	("5675159" | "5675185" | "5689136" | "5716861" | "5733792" | "5736446" | "5753542" | "5789792" | "5793090" | "5811323" | "5825066" | "5851869" | "5856225" | 5858843| "5908307" | "5915182" | "5915196" | "5936280" | "5953616" | "5960270" | "5985726" | "6008111" | "6017808" | "6025254" | "6031269" | "6030863" | "6033958" | "6037204").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 15:35

S13	28	("6051473" | "6057200" | "6083798" | "6072222" | "6080645" | "6087235" | "6090691" | "6096614" | "6103609" | "6110783" | "6110787" | "6124176" | "6137149" | 6150221| "6156613" | "6171910" | "6184097" | "6187642" | "6190977" | "6200867" | "6211026" | "6216357" | "6228722" | "6248637" | "6300203" | "6300201" | "6316357" | "6320228").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 15:41
S14	8	("6380043" | "4683645" | "4745082" | "4784718" | "4789644" | "4835112" | "4954867" | "4996574").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 15:43
S15	1847	@ad<"20040205" and (silicon adj germanium) near8 oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:24
S16	16	@ad<"20040205" and (silicon adj germanium) near8 oxide near8 strain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:24
S17	75	@ad<"20040205" and (silicon adj germanium) near8 oxide near8 strain$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 19:11
S18	0	@ad<"20040205" and (silicon adj germanium) near8 oxide near8 strain$2 and hydrogen adj bond$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:31
S19	315	@ad<"20040205" and (silicon adj germanium) near8 oxide and porous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 19:11
S20	282	@ad<"20040205" and (silicon adj germanium) and strain$2 and porous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 19:12

S21	257	@ad<"20040205" and (silicon adj germanium) and strain$2 and porous and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 19:12
S22	72	@ad<"20040205" and (silicon adj germanium) and strain$2 and porous and oxide and second near2 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:09
S23	1	("2004/0115900").URPN.	USPAT	OR	ON	2005/11/17 10:35
S24	72	@ad<"20040205" and (silicon adj germanium) and strain$2 and porous and oxide and second near2 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:35
S25	0	S24 and SMOS	USPAT	OR	ON	2005/11/17 10:35
S26	0	S24 and SMOS$3	USPAT	OR	ON	2005/11/17 10:35
S27	11	S24 and FET	USPAT	OR	ON	2005/11/17 10:35
S28	45	@ad<"20040205" and (SiGe (silicon adj germanium)) and strain$2 and porous and oxide and second adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:09
S29	30	S28 and (FET MOS MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:09
S30	72	@ad<"20040205" and (silicon adj germanium) and strain$2 and porous and oxide and second near2 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:09
S31	11	S30 and FET	USPAT	OR	ON	2005/11/17 14:09
S32	22	S29 not S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:13

S33	5720	SMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:14
S34	52	SMOS and strained	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:14
S35	18	S34 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:06
S36	1	S35 not micro.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:22
S37	2297	strain$2 near8 (transistor FET MOS MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:24
S38	891	(transistor FET MOS MOSFET) and strained near5 (channel source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:24
S39	625	(transistor FET MOS MOSFET) and (strained adj (silicon layer si)) near5 (channel source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 08:56
S40	566	S39 and (SiGe (silicon adj germanium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 17:46

S41	95	S40 and (source drain) adj extension	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:26
S42	80	S41 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 17:47
S43	43	S42 not micro.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 16:09
S44	2	"20040053477"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 16:57
S45	0	hydrogen adj bonding near5 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 16:57
S46	12	hydrogen adj bonding same wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 16:57
S47	88	S40 and (aperture opening hole via) near3 (SiGe (Si adj Ge) (silicion adj germanium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 17:47
S48	69	S47 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 17:47

S49	566	(transistor FET MOS MOSFET) and (strained adj (silicon layer si)) near5 (channel source drain)and (SiGe (silicon adj germanium) (si adj ge) adj cap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 08:58
S50	95	(transistor FET MOS MOSFET) and (strained adj (silicon layer si)) near5 (channel source drain) and (SiGe (silicon adj germanium) (si adj ge) adj cap) and (drain source) adj extension	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 09:01
S51	80	S50 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 09:02
S52	625	(transistor FET MOS MOSFET) and (strained adj (silicon layer si)) near5 (channel source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 09:01
S53	72	S52 and ((SiGe (silicon adj germanium) (si adj ge)) adj cap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 09:01
S54	60	S53 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 10:17
S56	7	(xiang and besser and ngo and wang).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 10:17
S57	151	438/938.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:06

S58	133	S57 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:54
S59	7	257/E29.193 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:32
S60	351	wafer adj bonding and (sige (silicon adj germanium) (si adj ge)) and strained	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:32
S61	254	S60 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:11
S62	0	("5108954" | "5120666" | "5168072" | "5200352" | "5202754" | "5258637" | "5264382" | "5320974" | "5321286" | "5346834" | "5374575" | "5391510" | "5393685" | "5420048" | "5429956" | "5451798" | "5481133" | "5482877" | "5491099" | "5497019" | "5516707" | "5581101" | "5593907" | "5595919" | "5607884" | "5612546" | "5612552" | "5654570").PN. and ((strain strained) near8 (channel source drain))	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29
S63	28	("5108954" | "5120666" | "5168072" | "5200352" | "5202754" | "5258637" | "5264382" | "5320974" | "5321286" | "5346834" | "5374575" | "5391510" | "5393685" | "5420048" | "5429956" | "5451798" | "5481133" | "5482877" | "5491099" | "5497019" | "5516707" | "5581101" | "5593907" | "5595919" | "5607884" | "5612546" | "5612552" | "5654570").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29

S64	27	("56751598" | "5675185" | "5689136" | "5716861" | "5733792" | "5736446" | "5753542" | "5789792" | "5793090" | "5811323" | "5825066" | "5851869" | "5856225" | 5858843| "5908307" | "5915182" | "5915196" | "5936280" | "5953616" | "5960270" | "5985726" | "6008111" | "6017808" | "6025254" | "6031269" | "6030863" | "6033958" | "6037204").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29
S65	28	("5675159" | "5675185" | "5689136" | "5716861" | "5733792" | "5736446" | "5753542" | "5789792" | "5793090" | "5811323" | "5825066" | "5851869" | "5856225" | 5858843| "5908307" | "5915182" | "5915196" | "5936280" | "5953616" | "5960270" | "5985726" | "6008111" | "6017808" | "6025254" | "6031269" | "6030863" | "6033958" | "6037204").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29
S66	28	("6051473" | "6057200" | "6083798" | "6072222" | "6080645" | "6087235" | "6090691" | "6096614" | "6103609" | "6110783" | "6110787" | "6124176" | "6137149" | 6150221| "6156613" | "6171910" | "6184097" | "6187642" | "6190977" | "6200867" | "6211026" | "6216357" | "6228722" | "6248637" | "6300203" | "6300201" | "6316357" | "6320228").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29
S67	8	("6380043" | "4683645" | "4745082" | "4784718" | "4789644" | "4835112" | "4954867" | "4996574").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29
S68	0	(S63 S64 S65 S66 S67) and ((strain strained) near8 (channel source drain))	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:30
S69	0	(S63 S64 S65 S66 S67) and (strain strained)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:29
S70	92	(S63 S64 S65 S66 S67)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:53
S71	146	strained adj silicon adj channel	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:54

S72	144	S71 and ((silicon adj germanium) sige (si adj ge))	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/18 13:54
S73	112	S72 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:08
S74	15	S73 and strained near2 (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:07
S75	10	(aperture opening) near2 ((silicon adj germanium) sige (si adj ge)) same gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:07
S76	10	S75 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:20
S77	7	S76 and (strain strained)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:16
S78	45	438/282.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:19
S79	53	window near2 ((silicon adj germanium) (si adj ge) (sige))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:19
S80	43	S79 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:30

S81	12	S80 and (strain or strained)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:30
S82	80	recessed adj gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:30
S83	77	S82 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:11
S84	1	S83 and (strain or strained)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:31
S85	43	438/525.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:07
S86	664	438/197.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:11
S87	508	S86 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:44
S88	8	trench adj transistor and (strain strained)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:44

S89	703	"trench transistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:44
S90	47	S89 and ((silicon adj germanium) sige (si adj ge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:44
S91	41	S90 and @ad<"20040205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:51
S92	1	@pn="5801075"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:51